

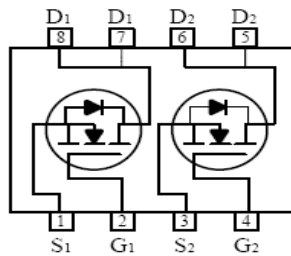
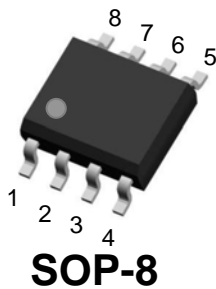


Dual N-Channel MOSFET (30V, 6.7A)

PRODUCT SUMMARY		
V _{DS}	I _D	R _{DS(on)} (m-ohm) Max
30V	6.9A	26 @ V _{GS} =10V, I _D =6.9A
		40 @ V _{GS} =4.5V, I _D =5.8A

Features

- Super high density cell design for extremely low RDS(ON)
- Exceptional on-resistance and maximum DC current capability
- Ordering information : KF4812 (Lead (Pb) -free)
KF4812-G (Lead (Pb) -free and halogen-free)



Pin 1: Source 2
Pin 2: Gate 2
Pin 3: Source 1
Pin 4: Gate 1
Pin 5 / 6: Drain 1
Pin 7 / 8: Drain 2

Absolute Maximum Ratings (T_A=25°C, unless otherwise noted)

Symbol	Parameter	Ratings	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current (Continuous) @T _A =25°C	6.9	A
	Drain Current (Continuous) @T _A =75°C	5.4	A
I _{DM}	Drain Current (Pulsed) ^a	30	A
P _D	Total Power Dissipation @T _A =25°C	2.0	W
	Total Power Dissipation @T _A =75°C	1.3	W
I _S	Maximum Diode Forward Current	1.7	A
T _j , T _{stg}	Operating Junction and Storage Temperature Range	-55 to +150	°C
R _{θJA}	Thermal Resistance Junction to Ambient (PCB mounted) ^b	62.5	°C/W

a: Repetitive Rating: Pulse width limited by the maximum junction temperature.
b: 1-in² 2oz Cu PCB board